Accurate modeling for drain breakdown current of GaAs MESFET's

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K. Fujii, Y. Hara, T. Yakabe and H. Yabe. "Accurate modeling for drain breakdown current of GaAs MESFET's." 1999 Transactions on Microwave Theory and Techniques 47.4 (Apr. 1999 [T-MTT]): 516-518.

Extensive measurements of a drain breakdown current as a function of device bias are reported in this paper. To represent the measured drain breakdown currents accurately, a new modeling function and an equivalent circuit controlled by two voltages are proposed. This model, when integrated into a large-signal analysis program, improves the accuracy of the simulation.

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